XBS013S16R-G



ETR1604-003

Schottky Barrier Diode, 100mA, 30V Type

■FEATURES

■APPLICATIONS

Forward Voltage : V_F=0.71V (TYP.) **Forward Current** : $I_{F(AV)}$ =100mA : V_{RM} =30VRepetitive Peak Reverse Voltage

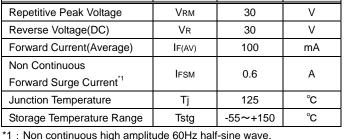
Low Current Rectification

Environmentally Friendly : EU RoHS Compliant, Pb Free

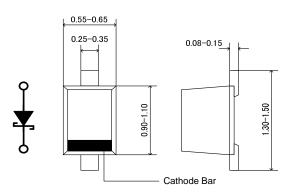
■ ABSOLUTE MAXIMUM RATINGS

■ PACKAGING INFORMATION

			Ta=25°C
PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive Peak Voltage	VRM	30	V
Reverse Voltage(DC)	VR	30	V
Forward Current(Average)	I F(AV)	100	mA
Non Continuous Forward Surge Current ^{*1}	İFSM	0.6	А
Junction Temperature	Tj	125	°C
Storage Temperature Range	Tstg	-55~+150	°C









SOD-723

■MARKING RULE



- ①: 0 (Product Number)
- 2: Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	DESCRIPTION		
XBS013S16R	SOD-723		
XBS013S16R-G	SOD-723 (Halogen & Antimony free)		

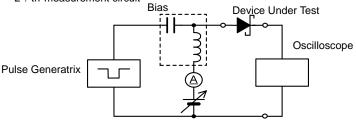
^{*} The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

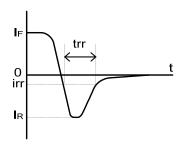
■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER SYM	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
	STIVIDOL	TEST CONDITIONS	MIN.	TYP.	MAX.	OINIT
Forward Voltage VF1 I _F =1mA		I _F =1mA	-	0.31	=	V
VF2	VF2	I _F =100mA	1	0.71	1	V
Reverse Current	lr	V _R =25V	ı	-	2	μΑ
Inter-Terminal Capacity	Ct	V _R =0V , f=1MHz	-	6	-	pF
Reverse Recovery Time*2	trr	I _F =I _R =10mA , irr=1mA	-	2	-	ns

*2 : trr measurement circuit



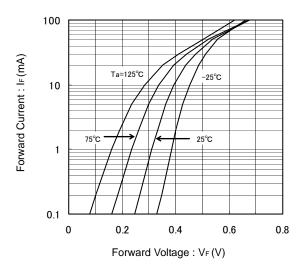


^{*} The device orientation is fixed in its embossed tape pocket.

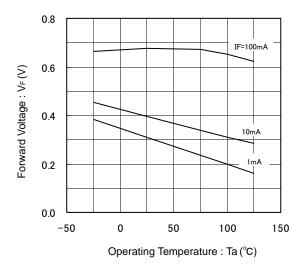
XBS013S16R-G

■TYPICAL PERFORMANCE CHARACTERISTICS

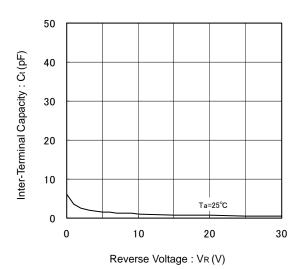
(1) Forward Current vs. Forward Voltage



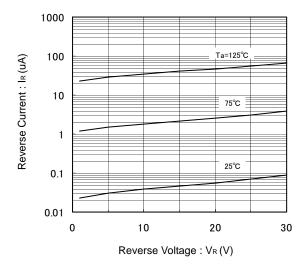
(3) Forward Voltage vs. Operating Temperature



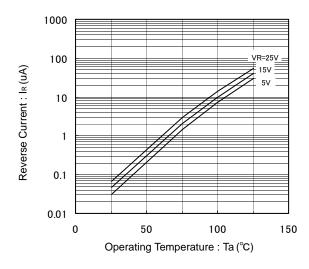
(5) Inter-Terminal Capacity vs. Reverse Voltage



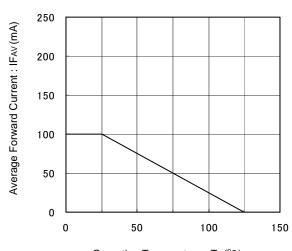
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



Operating Temperature : Ta (°C)

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